

Supplemental Document for Submission #14137

Title : Plasma Impedance Monitoring of SiNx Etching Processes with Different Grounding Conditions

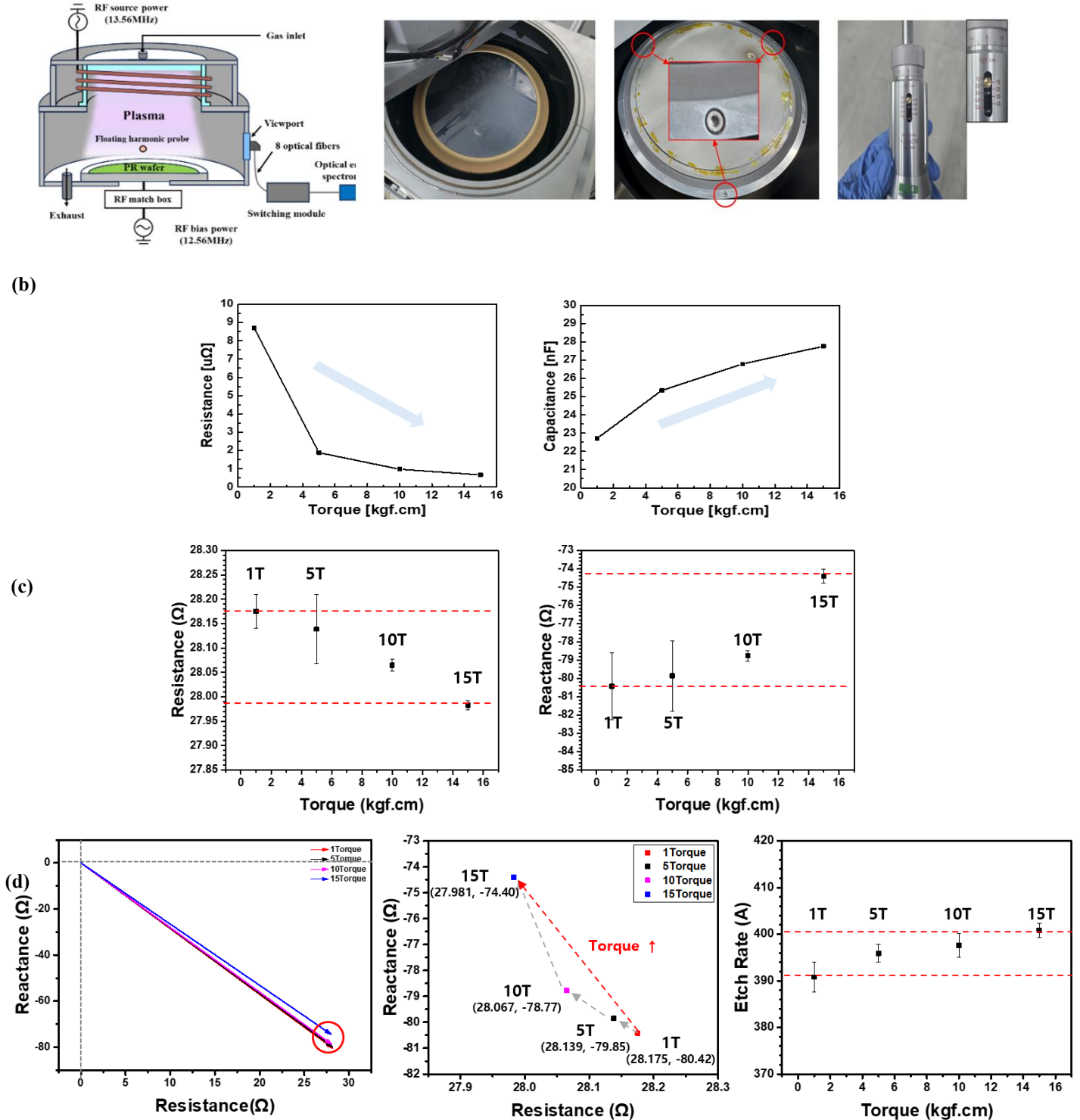


Fig. 1. (a) Scheme of the 300mm ICP chamber, Photographs of the plasma etch chamber hardware and the torque driver used for controlling the RF grounding interface tightening (b) Theoretical model of resistance and capacitance variations as a function of applied torque (c) Measured resistance and reactance obtained from VI probe diagnostics, representing the average values and standard deviations across different torque levels (d) Impedance analysis and SiN layer etch rate at different torque levels